

September 2013

# FGB7N60UNDF 600 V, 7 A Short Circuit Rated IGBT

#### **Features**

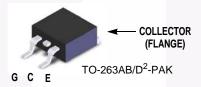
- Short Circuit Rated 10 us
- · High Current Capability
- High Input Impedance
- Fast Switching
- RoHS Compliant

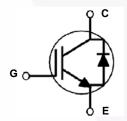
## **Applications**

• Sewing Machine, CNC, Home Appliances, Motor Control

## **General Description**

Using advanced NPT IGBT technology, Fairchild's the NPT IGBTs offer the optimum performance for low-power inverterdriven applications where low-losses and short-circuit ruggedness features are essential, such as sewing machine, CNC, motor control and home appliances.





## **Absolute Maximum Ratings**

Symbol	Description		Ratings	Unit	
V <sub>CES</sub>	Collector to Emitter Voltage		600	V	
$V_{GES}$	Gate to Emitter Voltage		± 20	V	
I <sub>C</sub>	Collector Current	$@ T_C = 25^{\circ}C$	14	Α	
.0	Collector Current	$@ T_C = 100^{\circ}C$	7	Α	
I <sub>CM (1)</sub>	Pulsed Collector Current @ T <sub>C</sub> = 25°C		21	A	
l <sub>F</sub>	Diode Forward Current	@ T <sub>C</sub> = 25°C	7	A	
	Diode Forward Current	$@ T_C = 100^{\circ}C$	3.5	Α	
P <sub>D</sub>	Maximum Power Dissipation	@ T <sub>C</sub> = 25°C	83	W	
	Maximum Power Dissipation	$@ T_C = 100^{\circ}C$	33	W	
T <sub>J</sub>	Operating Junction Temperature		-55 to +150	°C	
T <sub>stg</sub>	Storage Temperature Range		-55 to +150	°C	
TL	Maximum Lead Temp. for soldering Purposes, 1/8" from case for 5 seconds		300	°C	

#### Notes:

## **Thermal Characteristics**

Symbol	Parameter	Тур.	Max.	Unit
$R_{\theta JC}(IGBT)$	Thermal Resistance, Junction to Case		1.5	°C/W
$R_{\theta JC}(Diode)$	Thermal Resistance, Junction to Case		3.5	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient (PCB Mount)(2)		40	°C/W

#### Notes:

<sup>1:</sup> Repetitive rating: Pulse width limited by max. junction temperature

<sup>2:</sup> Mounted on 1" square PCB (FR4 or G-10 material)

# **Package Marking and Ordering Information**

Device Marking Device		Package	Rel Size	Tape Width	Quantity
FGB7N60UNDF	FGB7N60UNDF	DF TO-263AB(D <sup>2</sup> -PAK)		-	50

# Electrical Characteristics of the IGBT $T_C = 25$ °C unless otherwise noted

Symbol	Parameter	Test Conditions	Min.	Тур.	Max.	Unit
Off Charac	teristics					
BV <sub>CES</sub>	Collector to Emitter Breakdown Voltage	$V_{GE} = 0V, I_{C} = 250\mu A$	600	-	-	V
I <sub>CES</sub>	Collector Cut-Off Current	$V_{CE} = V_{CES}, V_{GE} = 0V$	-	-	1	mA
I <sub>GES</sub>	G-E Leakage Current	$V_{GE} = V_{GES}, V_{CE} = 0V$	-	-	±10	uA
On Charac	teristics					
V <sub>GE(th)</sub>	G-E Threshold Voltage	$I_C = 7mA$ , $V_{CE} = V_{GE}$	5.5	6.8	8.5	V
		I <sub>C</sub> = 7A, V <sub>GE</sub> = 15V	-	1.9	2.3	V
V <sub>CE(sat)</sub>	Collector to Emitter Saturation Voltage	I <sub>C</sub> = 7A, V <sub>GE</sub> = 15V, T <sub>C</sub> = 125°C	-	2.1	-	V
Dynamic C	haracteristics			!		
C <sub>ies</sub>	Input Capacitance		-	275		pF
C <sub>oes</sub>	Output Capacitance	$V_{CE} = 30V_{,} V_{GE} = 0V_{,}$ f = 1MHz	-	41		pF
C <sub>res</sub>	Reverse Transfer Capacitance	1 = 11VIITZ	-	10		pF
Switching	Characteristics					
t <sub>d(on)</sub>	Turn-On Delay Time		-	5.9		ns
t <sub>r</sub>	Rise Time		-	4.2		ns
t <sub>d(off)</sub>	Turn-Off Delay Time	$V_{CC} = 400V, I_{C} = 7A,$	-	32.3		ns
t <sub>f</sub>	Fall Time	$R_G = 10\Omega, V_{GE} = 15V,$	-	68	89	ns
E <sub>on</sub>	Turn-On Switching Loss	Inductive Load, T <sub>C</sub> = 25°C	-	99		uJ
E <sub>off</sub>	Turn-Off Switching Loss		-	104		uJ
E <sub>ts</sub>	Total Switching Loss		-	203		uJ
t <sub>d(on)</sub>	Turn-On Delay Time		- /	6		ns
t <sub>r</sub>	Rise Time		-	4.3		ns
t <sub>d(off)</sub>	Turn-Off Delay Time	$V_{CC} = 400V, I_{C} = 7A,$	-	33.8		ns
t <sub>f</sub>	Fall Time	$R_G = 10\Omega$ , $V_{GE} = 15V$ ,	-	113		ns
E <sub>on</sub>	Turn-On Switching Loss	Inductive Load, T <sub>C</sub> = 125°C	-	181		uJ
E <sub>off</sub>	Turn-Off Switching Loss		-	144		uJ
E <sub>ts</sub>	Total Switching Loss		-	325		uJ
T <sub>sc</sub>	Short Circuit Withstand Time	$V_{CC} = 350V,$ $R_G = 100\Omega, V_{GE} = 15V,$ $T_C = 150^{\circ}C$	10			us

# Electrical Characteristics of the IGBT $T_C = 25^{\circ}\text{C}$ unless otherwise noted

$Q_g$	Total Gate Charge		-	18	-	nC
$Q_{ge}$	Gate to Emitter Charge	$V_{CE} = 400V, I_{C} = 7A,$ $V_{GE} = 15V$	-	3	-	nC
Q <sub>qc</sub>	Gate to Collector Charge	VGE = 13 V	-	13	-	nC

# Electrical Characteristics of the Diode $T_C = 25^{\circ}C$ unless otherwise noted

Symbol	Parameter	Test Conditio	ns	Min.	Тур.	Max	Unit
V <sub>FM</sub> Diode Forward Voltage	Diode Forward Voltage	I <sub>F</sub> = 7A	$T_C = 25^{\circ}C$	-	1.7	2.2	V
	z.cac : o.ma.a : o.mage	·F · · · ·	$T_{\rm C} = 125^{\rm o}{\rm C}$	-	1.6		
t <sub>rr</sub>	Diode Reverse Recovery Time	$I_F = 7A$ , $dI_F/dt = 200A/\mu s$	$T_C = 25^{\circ}C$	-	32.3		ns
11			$T_{\rm C} = 125^{\rm o}{\rm C}$	-	70		
Q <sub>rr</sub>	Diode Reverse Recovery Charge		$T_C = 25^{\circ}C$	-	59		nC
			$T_{\rm C} = 125^{\rm o}{\rm C}$	-	172	-	

Figure 1. Typical Output Characteristics

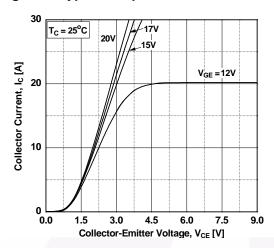


Figure 3. Typical Saturation Voltage Characteristics

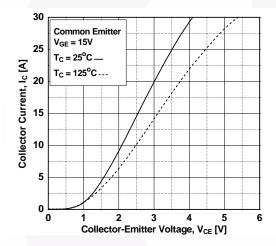
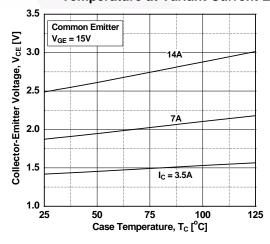


Figure 5. Saturation Voltage vs. Case
Temperature at Variant Current Level



**Figure 2. Typical Output Characteristics** 

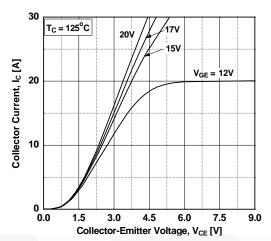


Figure 4. Transfer Characteristics

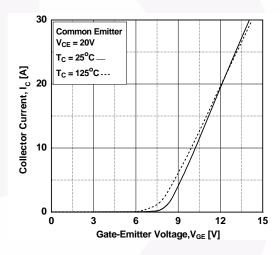


Figure 6. Saturation Voltage vs. V<sub>GE</sub>

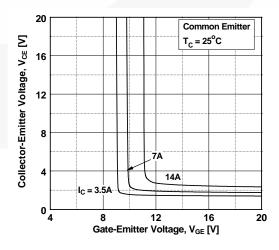


Figure 7. Saturation Voltage vs. V<sub>GE</sub>

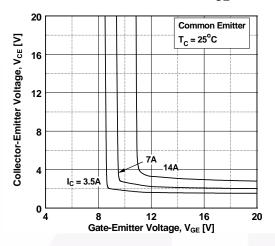


Figure 9. Gate charge Characteristics

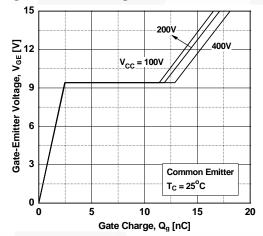


Figure 11. Turn-on Characteristics vs.
Gate Resistance

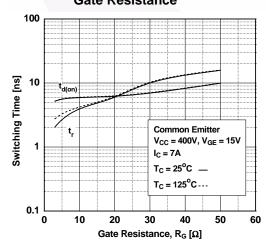


Figure 8. Capacitance Characteristics

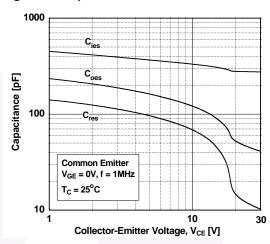


Figure 10. SOA Characteristics

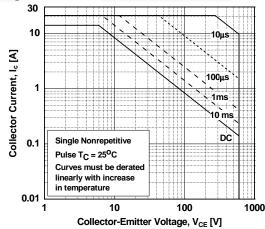


Figure 12. Turn-off Characteristics vs.
Gate Resistance

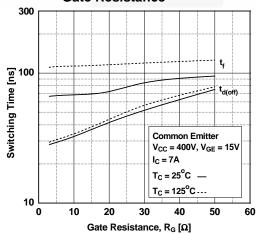


Figure 13. Turn-on Characteristics vs. Collector Current

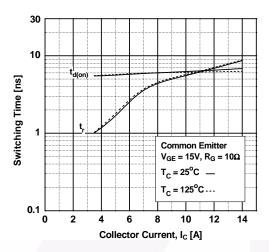


Figure 15. Switching Loss vs.
Gate Resistance

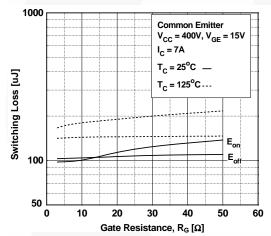


Figure 17. Turn off Switching SOA Characteristics

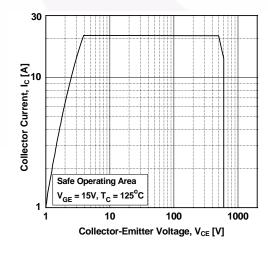


Figure 14. Turn-off Characteristics vs.
Collector Current

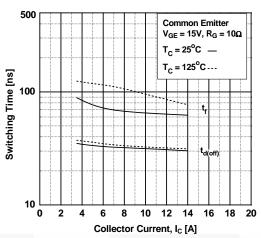
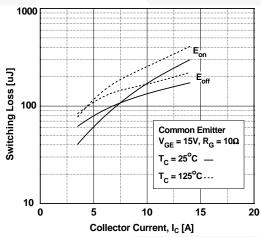


Figure 16. Switching Loss vs Collector Current



**Figure 18. Forward Characteristics** 

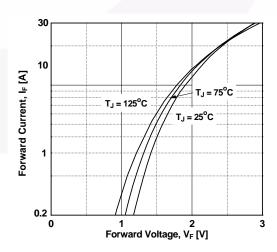


Figure 19. Reverse Current

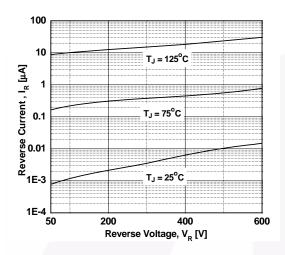


Figure 20. Stored Charge

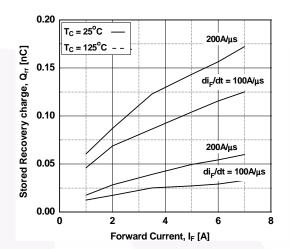


Figure 21. Reverse Recovery Time

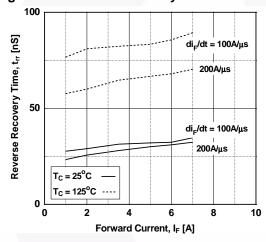
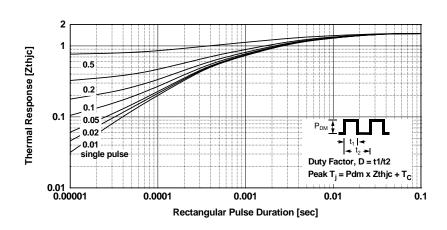


Figure 22. Transient Thermal Impedance of IGBT



# **Mechanical Dimensions** 9.45 10.00 (6.40)1.78 MAX 3.80 1,05 (2.12) -5.08 LAND PATTERN RECOMMENDATION UNLESS NOTED, ALL DIMS TYPICAL → 0.25 M B AM 5,08 6.22 MIN -6.86 MIN 15.88 14.61 SEE DETA**|**L A 2 NOTES; UNLESS OTHERWISE SPECIFIED A) ALL DIMENSIONS ARE IN MILLIMETERS. B) REFERENCE JEDEC, TO-263, VARIATION AB. C) DIMENSIONING AND TOLERANCING PER ANS| Y14,5M - 1994, D) LOCATION OF THE PIN HOLE MAY VARY GAGE PLANE (LOWER LEFT CORNER, LOWER CENTER AND CENTER OF THE PACKAGE). LANDPATTERN RECOMMENDATION PER IPC TO254P1524X482-3N 0.25 FILENAME: TO263A02REV6 ○ 0.10 B 2.79 0,25 MAX (5.38)SEATING PLANE

Figure 23. TO-263 2L (D2PAK) - 2LD,TO263, SURFACE MOUNT

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DETAIL A, ROTATED 90°

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Dimensions in Millimeters





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Rev. 166

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